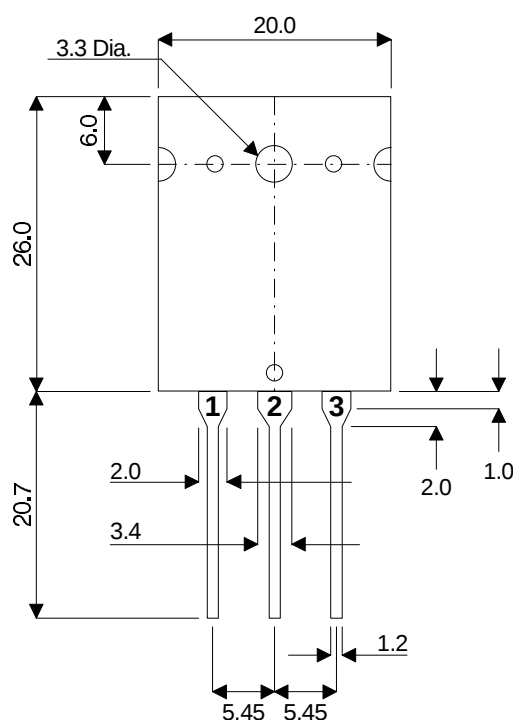


MECHANICAL DATA

Dimensions in mm

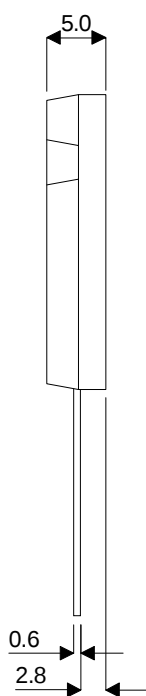


TO-3PBL

Pin 1 – Gate

Pin 2 – Source
Case is Source

Pin 3 – Drain



P-CHANNEL POWER MOSFET

POWER MOSFETS FOR AUDIO APPLICATIONS

FEATURES

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900DP & BUZ901DP
- DOUBLE DIE PACKAGE FOR MAXIMUM POWER AND HEATSINK SPACE

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}C$ unless otherwise stated)

		BUZ905DP	BUZ906DP
V_{DSX}	Drain – Source Voltage	-160V	-200V
V_{GSS}	Gate – Source Voltage	$\pm 14V$	
I_D	Continuous Drain Current	-16A	
$I_{D(PK)}$	Body Drain Diode	-16A	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	250W	
T_{stg}	Storage Temperature Range	-55 to $150^{\circ}C$	
T_j	Maximum Operating Junction Temperature	$150^{\circ}C$	
$R_{\theta JC}$	Thermal Resistance Junction – Case	$0.5^{\circ}C/W$	

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSX} Drain – Source Breakdown Voltage	V _{GS} = 10V	BUZ905DP	-160		V
	I _D = -10mA	BUZ906DP	-200		
BV _{GSS} Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14		V
V _{GS(OFF)} Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.1		V
V _{DS(SAT)*} Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -16A			V
I _{DSX} Drain – Source Cut-Off Current	V _{GS} = 10V	V _{DS} = -160V BUZ905DP			mA
		V _{DS} = -200V BUZ906DP			
yfs* Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	1.4		S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C _{iss} Input Capacitance	V _{DS} = 10V f = 1MHz		1900		pF
C _{oss} Output Capacitance			900		
C _{rss} Reverse Transfer Capacitance			60		
t _{on} Turn-on Time	V _{DS} = 20V		150		ns
t _{off} Turn-off Time	I _D = 7A		110		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

